TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

TPC8123

Lithium Ion Battery Applications Power Management Switch Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance: $R_{DS (ON)} = 7.0 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: |Y_{fs}| = 36 S (typ.)
- Low leakage current: $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode: V_{th} = -0.8 to -2.0 V (V_{DS} = -10 V, I_D = -0.5 mA)

	•	•	-		
Character	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	-30	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V _{DGR}	-30	V	
Gate-source voltage		V _{GSS}	-25/+20	V	
Drain current	DC (Note 1)	I _D	-11	٨	
Drain current	Pulse (Note 1)	I _{DP}	-44	A	
Drain power dissipatio	n (t = 10 s) (Note 2a)	PD	1.9	W	
Drain power dissipatio	n (t = 10 s) (Note 2b)	PD	1.0	W	
Single pulse avalanch	gle pulse avalanche energy (Note 3)		79	mJ	
Avalanche current	(Note 1)	I _{AR}	-11	А	
Repetitive avalanche energy (Note 2a) (Note 4)		E _{AR}	0.04	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature r	ange	T _{stg}	-55 to 150	°C	

Absolute Maximum Ratings (Ta = 25°C)

Note 1, Note 2, Note 3 and Note 4: See the next page.

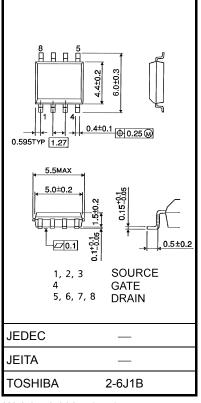
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature,

etc.) may cause this product to decrease in the reliability significantly

even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

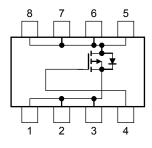
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.080 g (typ.)

Circuit Configuration



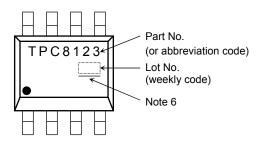
Unit: mm

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Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	125	°C/W

Marking (Note 5)



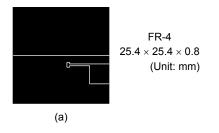
Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

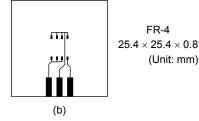
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Note 1: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}.$

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = -24$ V, $T_{ch} = 25$ °C (initial), L = 500 μ H, R_G = 25 Ω , I_{AR} = -11 A

- Note 4: Repetitive rating: pulse width limited by maximum channel temperature
- Note 5: on lower left of the marking indicates Pin 1.
 - Weekly code: (Three digits)



Week of manufacture

_(01 for the first week of a year: sequential number up to 52 or 53)

Year of manufacture (The last digit of a year)

Electrical Characteristics (Ta = 25°C)

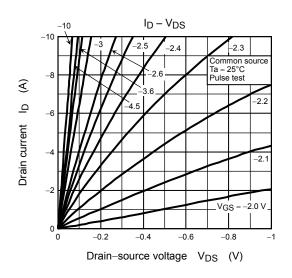
Char	acteristics	Symbol	Test Condition	Min			Unit
Gate leakage curre	ent	I _{GSS}	$V_{GS}=\pm 20~V,~V_{DS}=0~V$	_		±100	nA
Drain cut-OFF curr	rent	I _{DSS}	$V_{DS} = -30$ V, $V_{GS} = 0$ V	_	_	-10	μA
Drain agurag broad		V (BR) DSS	$I_{D} = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	V
Drain-source breakdown voltage		V (BR) DSX	$I_D = -10$ mA, $V_{GS} = 10$ V (Note 7)	-21		_	v
Gate threshold vol	tage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -0.5 \text{ mA}$	-0.8	_	-2.0	V
Drain source ON r	Drain-source ON-resistance		V_{GS} = -4.5 V, I _D = -5.5 A	_	9.5	12.5	- mΩ
Drain-source ON-I	esistance	R _{DS (ON)}	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -5.5 \text{ A}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	9.0		
Forward transfer admittance		Y _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -5.5 \text{ A}$	18	36	_	S
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	2940	_	pF
Reverse transfer capacitance		C _{rss}		_	460	_	
Output capacitance		C _{oss}		_	520	_	
	Rise time	tr	$V_{CS} = \frac{0}{10} = -5.5$ A	_	10	_	ns
Switching time	Turn-ON time	t _{on}	$V_{GS} \xrightarrow{0}_{-10} V \xrightarrow{I_D} \xrightarrow{I_D} \xrightarrow{-5.5A}_{-5} \xrightarrow{0} \boxplus \pi$		- ±100 - -10 - - - - - - - -2.0 9.5 12.5 7.0 9.0 36 - 2940 - 460 - 520 - 10 - 18 - 80 -	_	
Switching time	Fall time	t _f	ш.		80	_	
	Turn-OFF time	t _{off}	$V_{DD}\approx -15~V$ Duty \leq 1%, t_{W} = 10 μs	_	250	_	
Total gate charge (gate-source plus g	otal gate charge gate-source plus gate-drain)		V _{DD} ≈ -24 V, V _{GS} = -10 V,		68		
Gate-source charge 1		Q _{gs1}	$I_{\rm D} = -11 {\rm A}$		7		nC
Gate-drain ("miller') charge	Q _{gd}		_	18		

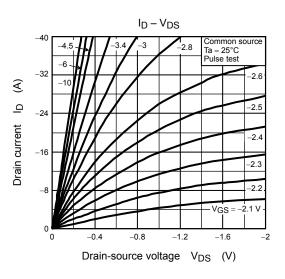
Source-Drain Ratings and Characteristics (Ta = 25°C)

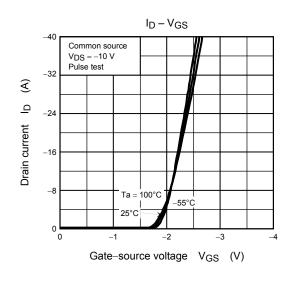
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	—	_	_	-44	А
Forward voltage (diode)		V _{DSF}	$I_{DR} = -11 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$			1.2	V	

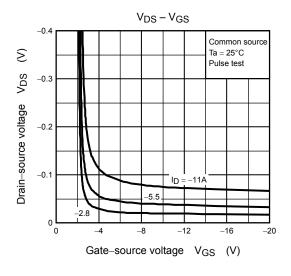
Note 7: VDSX mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

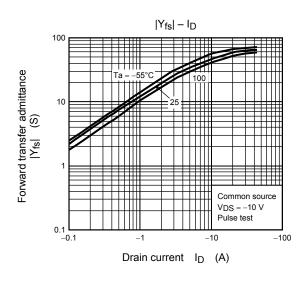
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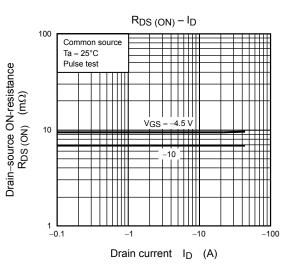








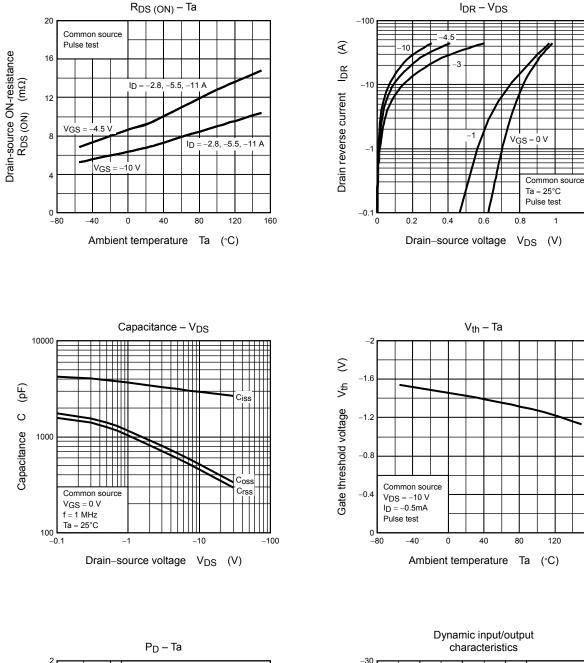


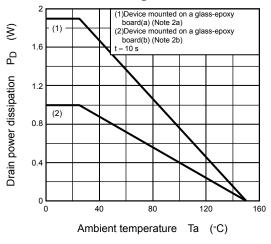


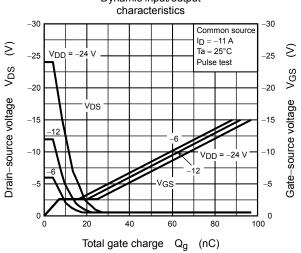
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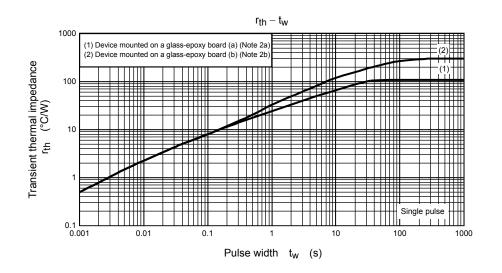
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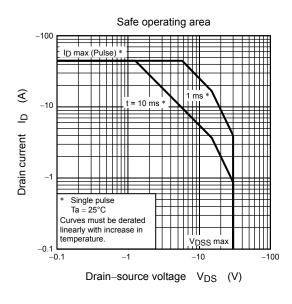
160











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